

600V Super-Junction Power MOSFET

FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

TO-220 GDS	TO-220F GDS	TO-251 _{G D S}	TO-252
RoHS	TO-262 GDS	TO-263 G ^D S	

Device Marking and Package Information						
Device	TPP60R580C	TPA60R580C	TPU60R580C	TPD60R580C	TPC60R580C	TPB60R580C
Package	TO-220	TO-220F	TO-251	TO-252	TO-262	TO-263
Marking	60R580C	60R580C	60R580C	60R580C	60R580C	60R580C

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
		Value			
Parameter	Symbol	TO-220, TO-251, TO-252 TO-262, TO-263 TO-220F		Unit	
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	600		V	
Continuous Drain Current	I _D	7		А	
Pulsed Drain Current (note1)	I _{DM}	21		А	
Gate-Source Voltage	V _{GSS}	±30		V	
Single Pulse Avalanche Energy (note2)	E _{AS}	162		mJ	
Avalanche Current (note1)	I _{AR}	1.4		А	
Repetitive Avalanche Energy (note1)	E _{AR}	0.2		mJ	
Power Dissipation ($T_c = 25^{\circ}C$)	P _D	63	28	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C	

Thermal Resistance					
		Value			
Parameter	Symbol	TO-220, TO-251, TO-252 TO-262, TO-263	TO-220F	Unit	
Thermal Resistance, Junction-to-Case	R_{thJC}	2.0	4.5	°C/W	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62	80	°C/W	

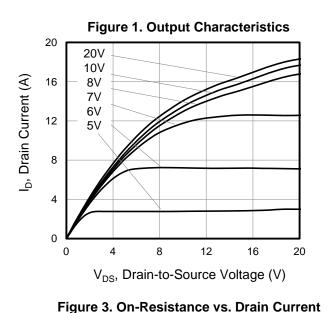


Specifications $T_J = 25^{\circ}C$, unless otherwise noted						
Parameter	Symbol	Symbol Test Conditions -	Value			Unit
Falameter	Symbol	Test conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250\mu A$	600			V
Zara Cata Valtaga Drain Currant	-	$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100	μA
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 30V$			±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 3A		0.5	0.58	Ω
Forward Transconductance (Note3)	9 _{fs}	$V_{DS} = 10V, I_{D} = 3A$		5		S
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 50V, f = 1.0MHz		587		
Output Capacitance	C _{oss}			31		pF
Reverse Transfer Capacitance	C _{rss}			4		
Total Gate Charge	Q _g			14.5		nC
Gate-Source Charge	Q _{gs}	$V_{DD} = 480V, I_D = 7A,$ $V_{GS} = 10V$		3		
Gate-Drain Charge	Q_{gd}			5.2		
Turn-on Delay Time	t _{d(on)}			39		
Turn-on Rise Time	t _r	V _{DD} = 400V, I _D = 7A,		25		ns
Turn-off Delay Time	t _{d(off)}	$R_{G} = 25\Omega$		100		
Turn-off Fall Time	t _f			18		
Drain-Source Body Diode Characteri	stics					
Continuous Body Diode Current	I _s	T _ 2500			6.3	۸
Pulsed Diode Forward Current	I _{SM}	T _C = 25°C			19	A
Body Diode Voltage	V _{SD}	$T_{J} = 25^{\circ}C, I_{SD} = 7A, V_{GS} = 0V$		0.9	1.2	V
Reverse Recovery Time	t _{rr}			250		ns
Reverse Recovery Charge	Q _{rr}	V _R = 480V, I _F = I _S , di _F /dt = 100A/µs		2.1		μC
Peak Reverse Recovery Current	l _{rrm}			16		А

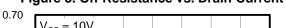
Notes

- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2. I_{AS} = 1.4A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 1%





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted



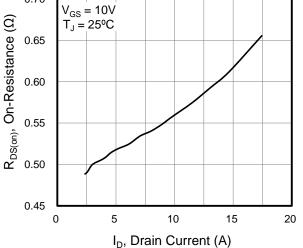
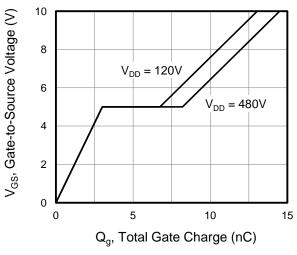
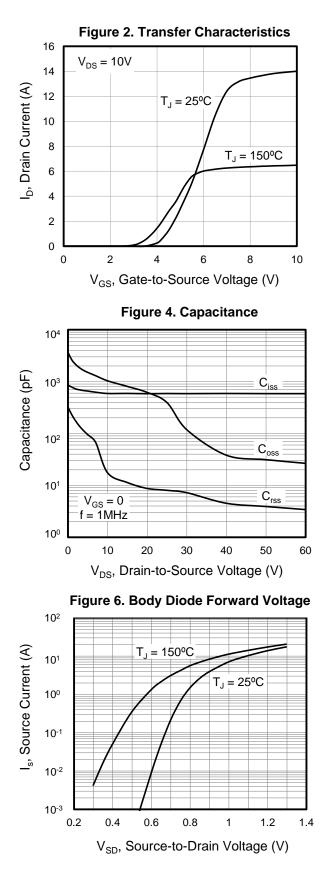
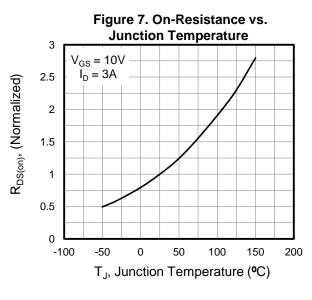


Figure 5. Gate Charge

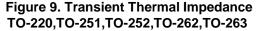


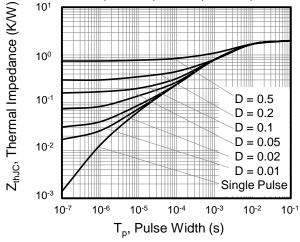






Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted





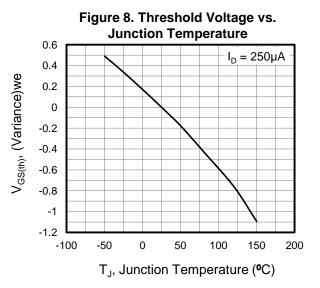
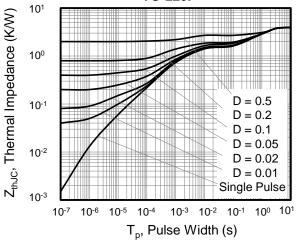
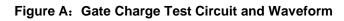


Figure 10. Transient Thermal Impedance TO-220F





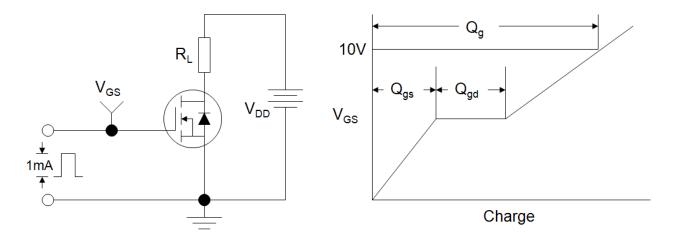


Figure B: Resistive Switching Test Circuit and Waveform

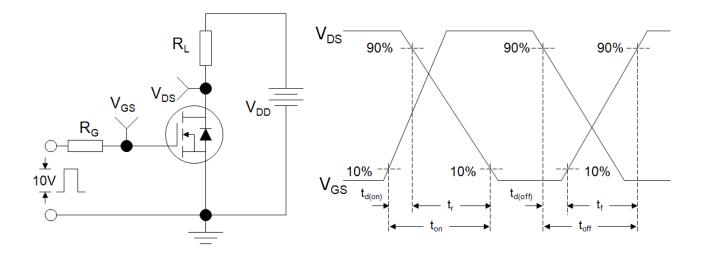
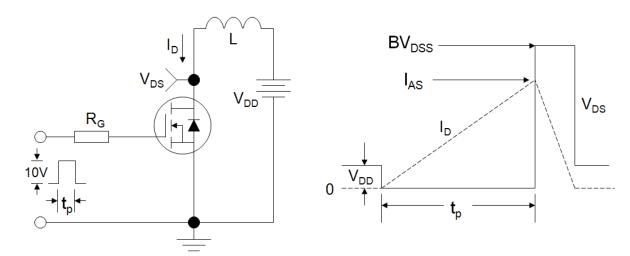
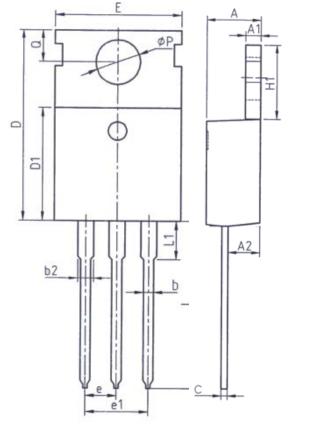


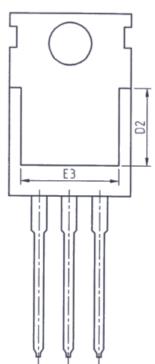
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-220

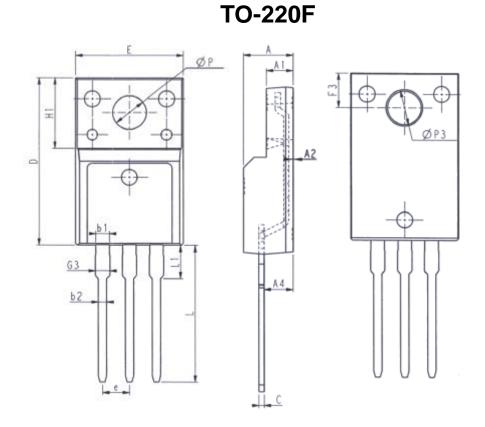




Unit: mm				
Symbol	Min.	Max.		
Α	4.37	4.77		
A1	1.25	1.45		
A2	2.20	2.60		
b	0.70	0.95		
b2	1.17	1.47		
c	0.40	0.65		
D	15.10	16. 10		
D1	8.80	9.40		
D2	5.50	-		

Unit: mm				
Symbol	Min.	Max.		
E	9.70	10. 30		
E3	7.00	-		
e	2. 54BSC			
e1	5. 08BSC			
H1	6. 25	6.85		
L	12.75	13.80		
L1	I	3. 40		
Р	3. 40	3.80		
Q	2.60	3.00		

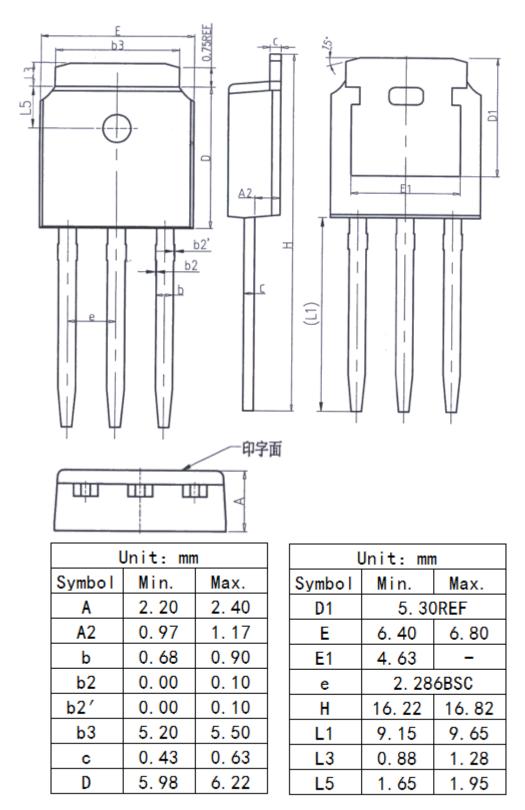




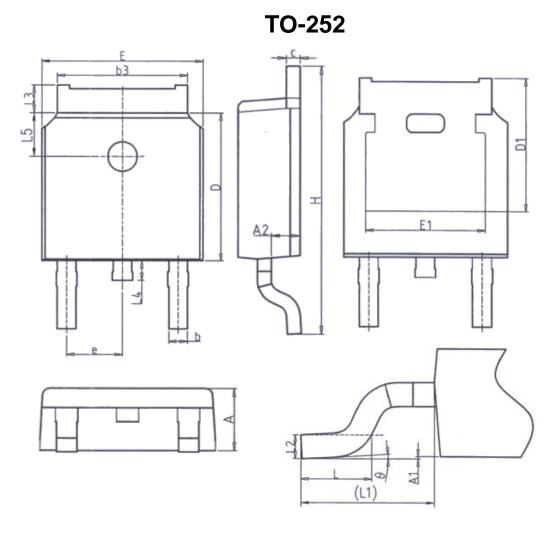
Unit: mm			l	Jnit: mn	n
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12. 68	13. 28
Α	4. 50	4.90	L1	2.93	3.13
A1	2.34	2.74	Р	3.03	3. 38
A2	0.30	0.60	P3	3. 15	3. 65
A4	2.56	2.96	F3	3. 15	3. 45
с	0.40	0.65	G3	1.25	1.55
D	15. 57	16. 17	b1	1.18	1.43
H1	6. 70REF		b2	0.70	0.95
e	2. 54BSC			-	









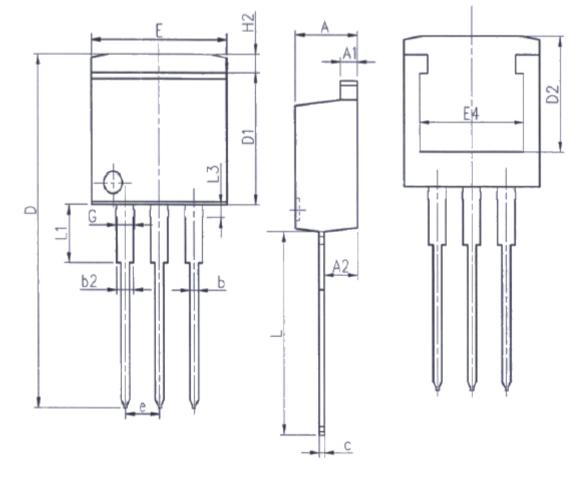


Un	Unit: mm				
Symbol	Min.	Max.			
Α	2.20	2.40			
A1	0.00	0.20			
A2	0.97	1.17			
b	0.68	0.90			
b3	5.20	5.50			
с	0.43	0.63			
D	5.98	6. 22			
D1	D1 5. 30REF				
E	6.40	6.80			
E1	4.63	-			

Unit: mm				
Symbol	Min.	Max.		
е	2. 286BSC			
Н	9.40	10. 50		
L	1.38	1.75		
L1	2.90REF			
L2	0, 51	BSC		
L3	0.88	1.28		
L4	-	1.00		
L5	1.65	1.95		
θ	0°	8°		



TO-262

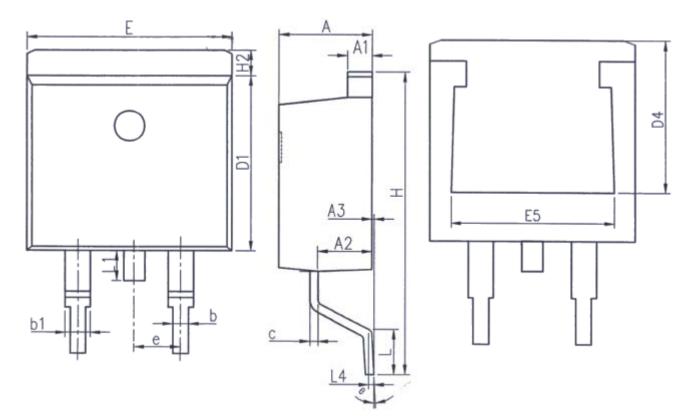


Unit: mm				
Symbol	Min.	Max.		
Α	4. 37	4. 77		
A1	1.22	1.42		
A2	2.47	2.87		
b	0.70	0.97		
b2	1.17	1.42		
с	0. 28	0.53		
D	23. 20	24. 02		
D1	8.38	8.90		
D2	6.00	-		

Unit: mm				
Symbol	Min.	Max.		
E	9.90	10.39		
E4	7.30	-		
e	2.54BSC			
G	1. 25	1.50		
H2	-	1.31		
L	13.34	14. 10		
L1	3.30	4.06		
L3	0.95	1.15		



TO-263



Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
Α	4. 37	4. 77	E	9.86	10.36
A1	1.22	1.42	E5	7.06	-
A2	2.49	2.89	e	2. 54BSC	
A3	0.00	0. 25	Н	14. 70	15. 50
b	0.70	0.96	H2	1.07	1.47
b1	1.17	1.47	L	2.00	2.60
с	0.30	0.53	L1	1.40	1.70
D1	8.50	8.90	L4	0. 25BSC	
D4	6. 60	-	θ	0°	9 °



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